- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages**

DB, DW, OR PW PACKAGE
(TOP VIEW)

description

This octal registered transceiver is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC543 contains two sets of D-type latches for temporary storage of data flowing in either direction. Separate latch-enable ($\overline{LEAB}$ or $\overline{LEBA}$) and output-enable ($\overline{OEAB}$ or $\overline{OEBA}$) inputs are provided for each register to permit independent control in either direction of data flow.

The A-to-B enable ($\overline{CEAB}$) input must be low to enter data from A or to output data from B. If $\overline{CEAB}$ is low and $\overline{LEAB}$ is low, the A-to-B latches are transparent; a subsequent low-to-high transition of $\overline{LEAB}$ places the A latches in the storage mode. With $\overline{CEAB}$ and $\overline{OEAB}$ both low, the 3-state B outputs are active and reflect the data present at the output of the A latches. Data flow for B to A is similar to that of A to B but uses $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

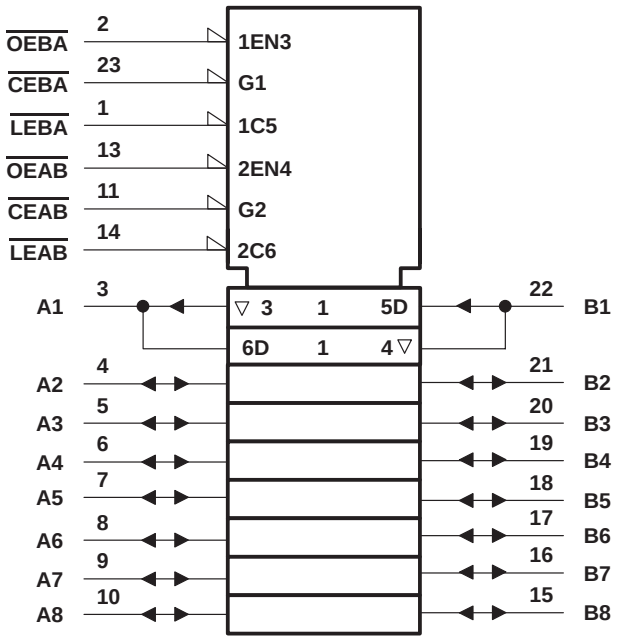
The SN74LVC543 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE†

INPUTS				OUTPUT
$\overline{CEAB}$	$\overline{LEAB}$	$\overline{OEAB}$	A	B
H	X	X	X	Z
X	X	H	X	Z
L	H	L	X	B_0‡
L	L	L	L	L
L	L	L	H	H

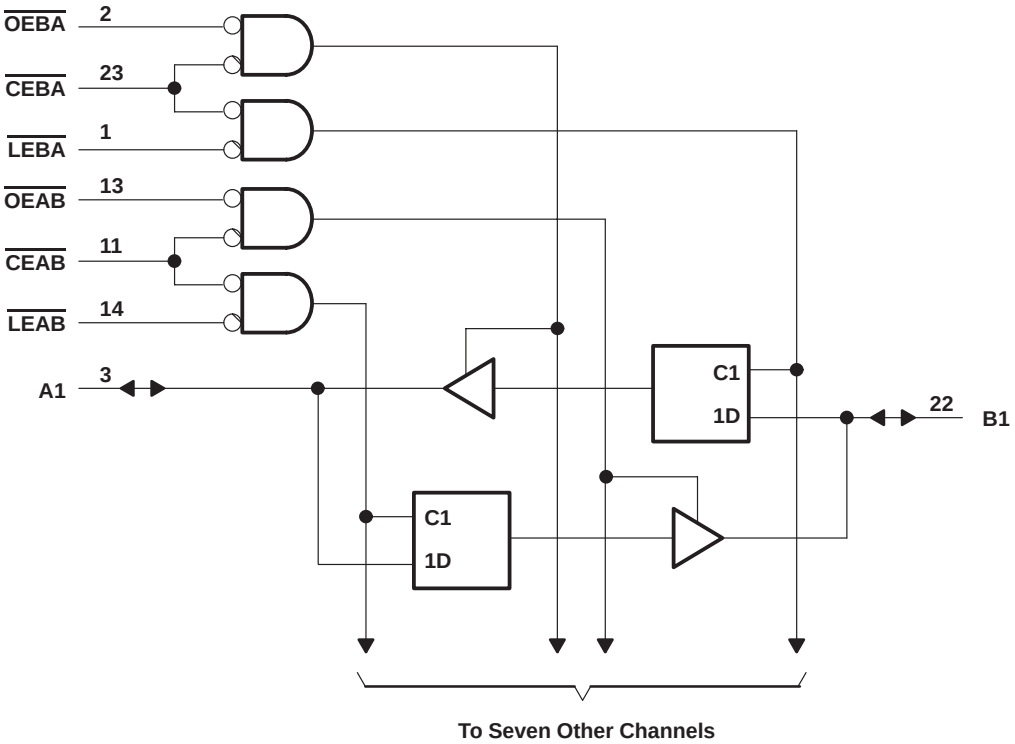
† A-to-B data flow is shown; B-to-A flow control is the same except that it uses $\overline{CEBA}$, $\overline{LEBA}$, and $\overline{OEBA}$.
‡ Output level before the indicated steady-state input conditions were established

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 6.5 V
I/O ports (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package . . . . . 0.65 W
DW package . . . . . 1.7 W
PW package . . . . . 0.7 W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2.7	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage	Control inputs	0	5.5	V
		Data inputs	0	V_{CC}	
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}		I_{OH} = –100 μA		MIN to MAX	V_{CC} – 0.2			V
		I_{OH} = – 12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = – 24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 μA		MIN to MAX			0.2	V
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		V_I = 5.5 V or GND		3.6 V			±5	μA
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			20	μA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			500	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		4.6		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		7.2		pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted)

		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
		MIN	MAX	MIN	MAX	
t_w	Pulse duration	4		4		ns
t_{su}	Setup time, data before $\overline{LE}$↑ or $\overline{CE}$↑	1.5		1.5		ns
t_h	Hold time, data after $\overline{LE}$↑ or $\overline{CE}$↑	2.5		2.5		ns

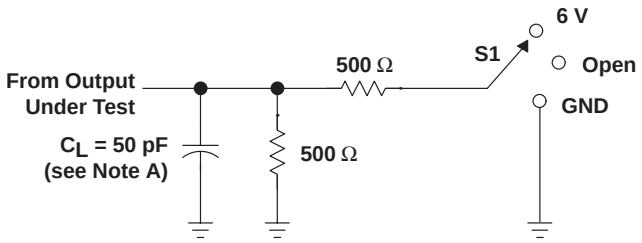
switching characteristics over recommended operating free-air temperature range, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	
t_{pd}	A or B	B or A	1.5	8		9	ns
	$\overline{LE}$		1.5	9.5		10.5	
t_{en}	$\overline{OE}$	A or B	1.5	8.5		9.5	ns
	$\overline{CE}$		1.5	9		10	
t_{dis}	$\overline{OE}$	A or B	1.5	8.5		9.5	ns
	$\overline{CE}$		1.5	9		10	

operating characteristics, V_{CC} = 3.3 V, T_A = 25°C

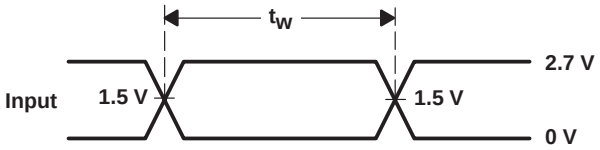
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 50 pF, f = 10 MHz	32	pF
		Outputs disabled		4.6	

PARAMETER MEASUREMENT INFORMATION

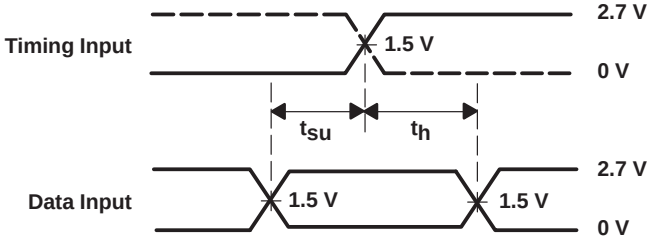


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

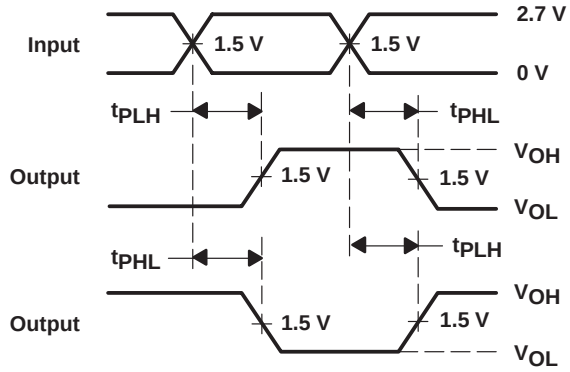
LOAD CIRCUIT FOR OUTPUTS



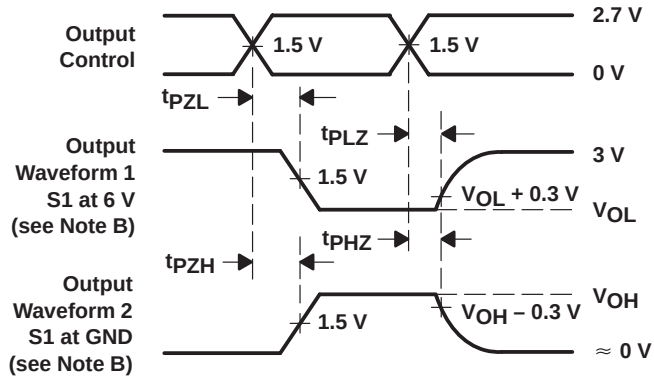
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 1. Load Circuit and Voltage Waveforms

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